

WEST Search History

DATE: Wednesday, June 25, 2003

| <u>Set Name</u> side by side | <u>Query</u> | <u>Hit Count</u> | <u>Set Name</u> result set |
|--|------------------------------|------------------|-------------------------------|
| <i>DB=USPT,PGPB,JPAB,EPAB,DWPI,TDBD; PLUR=YES; OP=OR</i> | | | |
| L15 | 14 and 111 | 63 | L15 |
| L14 | 112 and 113 | 202 | L14 |
| L13 | source and drain | 247069 | L13 |
| L12 | 110 and 111 | 202 | L12 |
| L11 | ldd or (light\$4 adj dop\$4) | 25721 | L11 |
| L10 | 17 and 19 | 230 | L10 |
| L9 | 18 adj4 drain | 457 | L9 |
| L8 | double adj diffus\$4 | 3977 | L8 |
| L7 | spacer\$ | 312447 | L7 |
| L6 | sapcer\$ | 62 | L6 |
| L5 | 11 and 14 | 1 | L5 |
| L4 | 13 adj3 drain | 81 | L4 |
| L3 | double adj dop\$4 | 262 | L3 |
| L2 | 5716861 | 53 | L2 |
| L1 | 5716861 | 53 | L1 |

END OF SEARCH HISTORY

End of Result Set



Generate Collection

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L2: Entry 1 of 1

File: DWPI

Oct 22, 2002

DERWENT-ACC-NO: 1998-569916
 DERWENT-WEEK: 200273
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TITLE: Open structure, especially photonic crystal production - by etching selectively doped layers of material having doping-dependent etchability

INVENTOR: GRUENING, U; LEHMANN, V ; REISINGER, H ; STENGL, R ; WENDT, H

PATENT-ASSIGNEE: SIEMENS AG (SIEI), INFINEON TECHNOLOGIES AG (INFN)

PRIORITY-DATA: 1997DE-1043296 (September 30, 1997)

PATENT-FAMILY:

| PUB-NO | PUB-DATE | LANGUAGE | PAGES | MAIN-IPC |
|-----------------|-------------------|----------|-------|-------------|
| US 6468348 B1 | October 22, 2002 | | 000 | C30B025/04 |
| DE 19743296 C1 | November 12, 1998 | | 006 | B32B001/10 |
| WO 9917349 A1 | April 8, 1999 | G | 000 | H01L021/306 |
| KR 2001030753 A | April 16, 2001 | | 000 | H01S003/08 |
| JP 2001518707 W | October 16, 2001 | | 018 | H01L021/306 |

DESIGNATED-STATES: JP KR US AT BE CH CY DE DK ES FI FR GB GR IE IT LU MC NL PT SE

APPLICATION-DATA:

| PUB-NO | APPL-DATE | APPL-NO | DESCRIPTOR |
|---------------|--------------------|----------------|------------|
| US 6468348B1 | August 21, 1998 | 1998WO-DE02450 | Cont of |
| US 6468348B1 | March 30, 2000 | 2000US-0539237 | |
| DE 19743296C1 | September 30, 1997 | 1997DE-1043296 | |
| WO 9917349A1 | August 21, 1998 | 1998WO-DE02450 | |
| KR2001030753A | March 28, 2000 | 2000KR-0703309 | |
| JP2001518707W | August 21, 1998 | 1998WO-DE02450 | |
| JP2001518707W | August 21, 1998 | 2000JP-0514317 | |
| JP2001518707W | | WO 9917349 | Based on |

INT-CL (IPC): B32 B 1/10; B32 B 31/10; C23 F 1/02; C30 B 25/02; C30 B 25/04; C30 B 31/06; C30 B 33/10; G02 B 1/02; G02 B 6/12; H01 L 21/306; H01 S 3/08

ABSTRACTED-PUB-NO: DE 19743296C
 BASIC-ABSTRACT:

Production of an open structure (3), consisting of two-dimensionally structured layers of material with doping-dependent etchability, involves: (a) preparing a first layer and doping one or more zones to mark a structure portion; (b) applying one or more further layers and doping one or more zones of the layer(s) to mark a structure portion; and (c) etching away each non-marked portion. Preferably, the material is a semiconductor (especially silicon) in single crystal form for the first layer and in epitaxially grown form for the further layer(s) and selective

p-doping is carried out with boron using masks.

USE - Used for producing a photonic crystal useful for confining optical waveguides or optical cavity resonators.

ADVANTAGE - The process produces an open monolith with a no more than fourfold periodically repetitive structure by means of semiconductor device technology thus allowing integration of photonic crystal technology with semiconductor optoelectronics technology.

ABSTRACTED-PUB-NO: DE 19743296C
EQUIVALENT-ABSTRACTS:

CHOSEN-DRAWING: Dwg.1/5

DERWENT-CLASS: L03 P73 P81 U11 V07 V08
CPI-CODES: L03-G02; L04-A01;
EPI-CODES: U11-C18B9; V07-F01A5; V08-A01A;